

L Number	Hits	Search Text	DB	Time stamp
-	274	156/345.12 156/345.13 156/345.16	USPAT	2003/09/04 10:29
-	13915	(polishing planariz\$5) same (grind\$3 condition\$3)	USPAT	2003/09/04 10:30
-	1270	("chemical mechanical" adj (polishing planariz\$5) same (grind\$3 condition\$3))	USPAT	2003/09/04 10:32
-	0	((("chemical mechanical" adj (polishing planariz\$5) same (grind\$3 condition\$3))) same ((analyz\$3 monitor\$3) adj3 (slurry solution)))	USPAT	2003/09/04 10:34
-	10	((("chemical mechanical" adj (polishing planariz\$5) same (grind\$3 condition\$3))) same ((analyz\$3 monitor\$3) same (slurry solution)))	USPAT	2003/09/04 10:42
-	3517	("ammonium citrate" "nitric acid") same (cu copper)	USPAT	2003/09/04 10:48
-	559	((("ammonium citrate" "nitric acid") same (cu copper)) and (polish\$3 abrad\$3 planariz\$5))	USPAT	2003/09/04 10:49
-	53	chopra-dinesh.in. meikle-scott.in.	USPAT	2003/09/04 12:59
-	1111	micron.as. and (condition\$3 dress\$3) and (analy\$4 monitor\$3)	USPAT	2003/09/04 13:00
-	261	micron.as. and (condition\$3 dress\$3) same (analy\$4 monitor\$3)	USPAT	2003/09/04 14:10
-	305	(polish\$3 abrad\$3) same (gas air) same (spring)	USPAT	2003/09/04 14:12
-	2	("chemical mechanical" adj (polish\$3 abrad\$3)) same (gas air) same (spring)	USPAT	2003/09/04 14:32
-	2422	("chemical mechanical" adj (polish\$3 abrad\$3)) same (dry plasma)	USPAT	2003/09/04 14:17
-	70	((("chemical mechanical" adj (polish\$3 abrad\$3)) same (dry plasma)) and (spring or "pressure releasing"))	USPAT	2003/09/04 14:17
-	3598	((dry plasma) same (polish\$3 abrad\$3 planariz\$5))	EPO; JPO; DERWENT	2003/09/04 14:33
-	654	((dry plasma) adj5 (polish\$3 abrad\$3 planariz\$5))	EPO; JPO; DERWENT	2003/09/04 14:33
-	143	((((dry plasma) adj5 (polish\$3 abrad\$3 planariz\$5))) and (wafer semiconductor))	EPO; JPO; DERWENT	2003/09/04 14:50
-	11	((((dry plasma) adj5 (polish\$3 abrad\$3 planariz\$5))) and (wafer semiconductor) and (spring pressure))	USPAT; EPO; JPO; DERWENT	2003/09/04 14:51
-	1138	134/113 134/104.1	USPAT	2003/09/05 14:41
-	21	(134/113 134/104.1) and (dress\$3 grind\$3 condition\$3 clean\$3) near5 (pad cloth platen)	USPAT	2003/09/05 14:41
-	55	156/345.13.ccls.	USPAT	2004/01/07 10:48
-	890	((dress\$3 clean\$3 condition\$3) with (pad cloth)) same (CMP "chemical mechanical")	USPAT	2004/01/07 12:56
-	114	((((dress\$3 clean\$3 condition\$3) with (pad cloth)) same (CMP "chemical mechanical")) and ((analy\$3 monitor\$3 test\$3) with (condition\$3 dress\$3 clean\$3)))	USPAT	2004/01/07 12:57
-	1	6736926.pn.	USPAT	2004/08/30 10:27
-	2529	156/345.13 134/113 134/104.1 156/345.12 451/66 451/443 451/444	USPAT	2004/08/30 14:25
-	1090	(156/345.13 134/113 134/104.1 156/345.12 451/66 451/443 451/444) and (dress\$3 clean\$3 rins\$3 wash\$3) with (pad cloth surface)	USPAT	2004/08/30 10:33
-	1049	(156/345.13 134/113 134/104.1 156/345.12 451/66 451/443 451/444) and (polish\$3 abrad\$3)	USPAT	2004/08/30 10:33
-	508	(156/345.13 134/113 134/104.1 156/345.12 451/66 451/443 451/444) and ((dress\$3 clean\$3 rins\$3 wash\$3) with (pad cloth surface) same (abrad\$3 polish\$3))	USPAT	2004/08/30 11:40
-	149	(condition\$3 dress\$3) same (polish\$3 abrad\$3) same ((monitor\$3 sens\$3 detect\$3 measur\$3) with (torqu\$3 force))	USPAT	2004/08/30 14:13

-	50	(condition\$3 dress\$3) same (polish\$3 abrad\$3) same ((monitor\$3 sens\$3 detect\$3 measur\$3) with(torqu\$3 force))	EPO; JPO; DERWENT	2004/08/30 14:25
-	40	(156/345.13 134/113 134/104.1 156/345.12 451/66 451/443 451/444)and ((condition\$3 dress\$3) same (monitor\$3 detect\$3 sens\$3) with (force torqu\$3))	USPAT	2004/08/30 14:27